

FIG.1A  
CONVENTIONAL ART

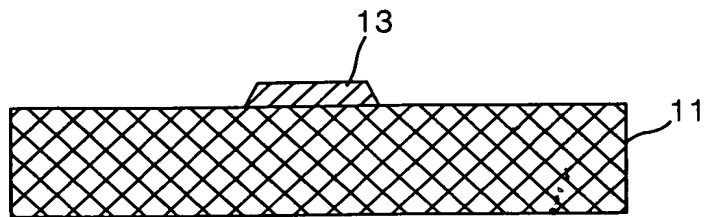


FIG.1B  
CONVENTIONAL ART

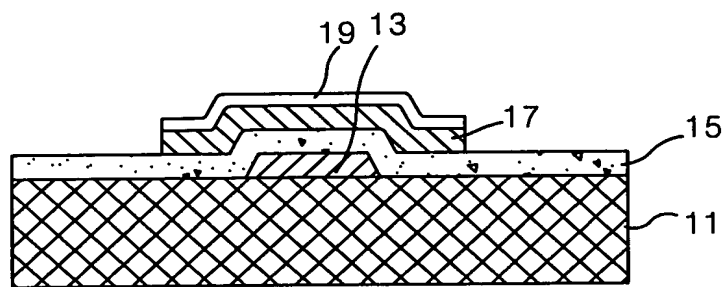


FIG.1C  
CONVENTIONAL ART

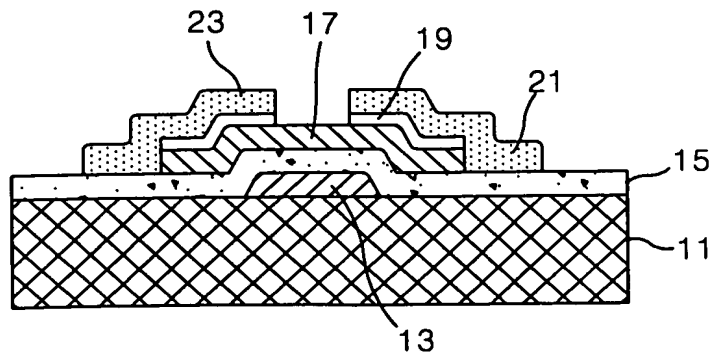


FIG.1D  
CONVENTIONAL ART

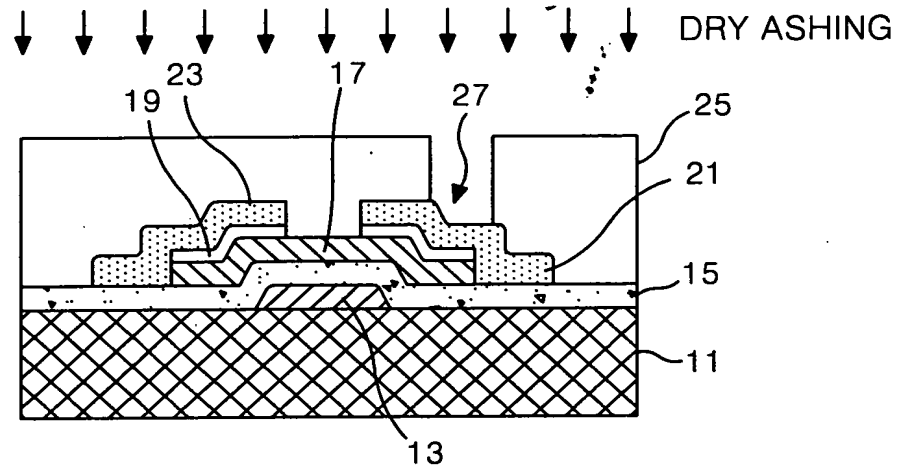
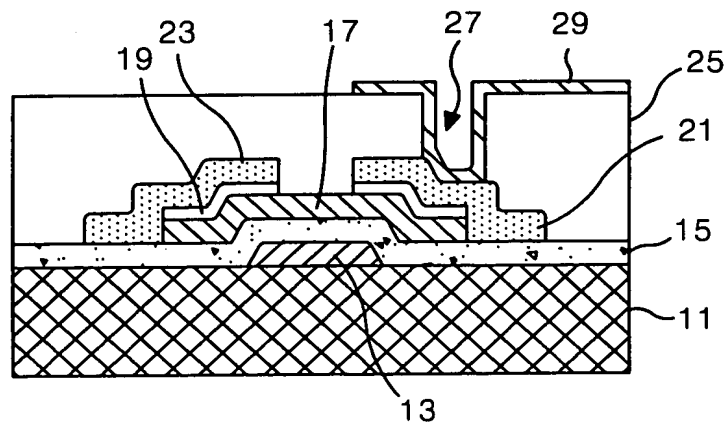
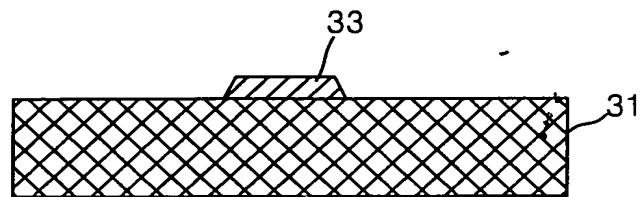


FIG.1E  
CONVENTIONAL ART



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A cross-sectional view of a semiconductor device. It features a substrate 31 with a cross-hatched pattern. A thin layer 35 is deposited on top of the substrate. A patterned layer 37 is formed on the thin layer 35, with a central opening 33. A top layer 39 is deposited on the patterned layer 37, filling the opening 33.

Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 31 with a cross-hatch pattern, a thin layer 35, and a series of stacked layers 33, 37, 39, and 43. A central opening 41 is present in the upper layers.

FIG.2D

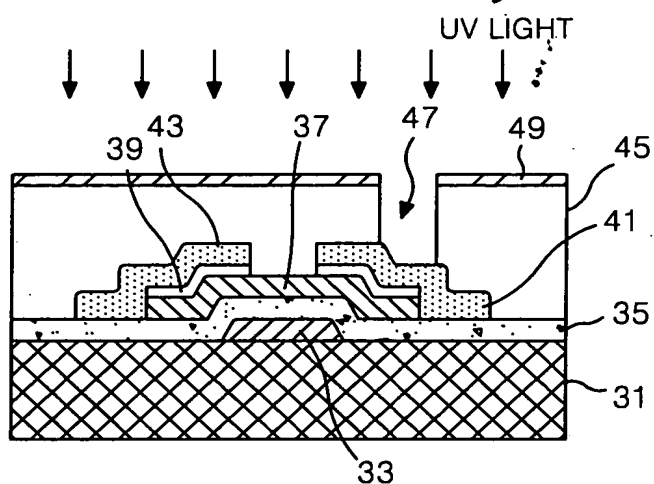


FIG.2E

